In the Specification:

Please amend paragraph 0030 on page 11 as follows:

The first dielectric material 112 comprises the portion of the second insulating layer 110 in which vias will be formed, in a dual damascene method. Thus, the first dielectric material 112 comprises a via dielectric material or via insulating layer. If the first conductive lines 106 comprise copper, preferably, the first dielectric material [[114]] 112 comprises a material having a coefficient of thermal expansion (CTE) that is close to the CTE of copper, or the CTE of the first conductive lines 106, to prevent shearing or breaks in the electrical connection of the via to underlying first conductive lines over temperature-induced stress.

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